



3DD511

NPN Silicon Low Frequency High Power Transistor



Features:

1. Heavy output current.Small saturation voltage drop.Good output character.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Collector-Emitter Voltage	V_{CEO}	V	250	
Emitter-Base Voltage	V_{EBO}	V	5	
Max. Collector Current	I_{CM}	A	10	
Max. Collector Dissipation	P_{CM}	W	100	($T_c=75^\circ\text{C}$)
Junction Temperature	T_{jm}	$^\circ\text{C}$	175	
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175	
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:2.0	$V_{CE}=125\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.2	$I_c=5\text{A}, I_b=0.5\text{A}$
DC Current Gain	h_{FE}		Max.:80, Min.:40	$V_{CE}= 5\text{V}, I_c=3.5\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	250	$I_c=5\text{mA}$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5	$I_E=5\text{mA}$

Outline and Dimensions: